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SEMICONDUCTOR DEVICE AND FABRICATION METHOD THEREOF

ABSTRACT OF THE DISCLOSURE

For forming a gate electrode, a conductive film with low resistance including Al or a material containing Al as its main component and a conductive film with low contact resistance for preventing diffusion of Al into a semiconductor layer are laminated, and the gate electrode is fabricated by using an apparatus which is capable of performing etching treatment at high speed.

(Fig. 1D)

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